

ABSTRACT

A method for manufacturing a semiconductor device is provided including: a step of forming a solid barrier metal layer on an interlayer insulating film; a removing step of removing at least a part of the solid barrier metal layer located at a place at which a pad opening portion is to be formed; a step of forming a solid second Al alloy film on the interlayer insulating film exposed in the removing step described above and the solid barrier metal layer; a step of patterning the solid second Al alloy film and the solid barrier metal layer so as to form a bonding pad portion on the interlayer insulating film; a step of forming a passivation film on the bonding pad portion and the interlayer insulating film; and a step of forming the pad opening portion in the passivation film at a position located on the bonding pad portion.